SUNDAY (5TH AUGUST)	
17.00	**Registration starts (open during entire event)**
18.00-20.00	**Get together**

MONDAY (6TH AUGUST)		
8.45-9.00	**Opening Ceremony (I. Grzegory)**	
9.00-10.40	**Plenary Session 1** **PS1** (chair: **Y Nanishi**)	
9.00-9.50	Anniversary Lecture: S. Porowski – Is the phase diagram of GaN anomalous in respect to other tetrahedrally bonded semiconductors? **(plenary) PS1.1**	
9.50 - 10.40	S. Nakamura - LED and Laser Diodes **(plenary) PS1.2**	
10.40-11.10	**Coffee break**	
11.10-12.50	**Plenary Session 2** **PS2** (chair: **T. Suski**)	
11.10-12.00	H. Amano – Transformative Electronics Based on GaN and Related Materials for Realizing Sustainable Smart Society **(plenary) PS2.1**	
12.00-12.50	Z. Sitar - AlGaN - a semiconductor that nature has never intended **(plenary) PS2.2**	
13.00-14.00	**Lunch break**	
14.00-16.00	**Parallel sessions: Growth and Characterization & Optoelectronic Devices**	
	Mo1 - G&CH (chair: **J. Suda**)	**Mo2 - OPTO** (chair: **V. Jmerik**)
14.00-14.30	H. Fujikura - HVPE as A New Tool for Homo-Epitaxial Growth of Highly-Pure and Thick GaN Drift Layers for Power Devices (**invited**) **Mo1.1**	H. Hirayama - Recent progress of AlGaN deep-UV LEDs by increasing light-extraction efficiency (**invited**) **Mo2.1**
14.30-15.00	Ke Xu - Growth of GaN substrate by HVPE, progress and challenge (**invited**) **Mo1.2**	S. Hagedorn - Influence of AlN/sapphire substrate properties on growth and performance of AlGaN-based UV LEDs (**invited**) **Mo2.2**
15.00-15.30	T. Sochacki - Recent progress in HVPE-GaN growth on ammonothermally grown GaN seeds (**invited**) **Mo1.3**	Y. Park - 375-nm Optically Pumped Vertical-Cavity Surface-Emitting Lasers with Air-Gap/Al0.05Ga0.95N Distributed Bragg Reflectors **(invited) Mo2.3**
15.30-15.45	T. Baker - HVPE Growth of Free-Standing GaN Wafers by Interlayer Separation **Mo1.4**	J. Enslin - Growth of InAlGaN for efficient UVB light emitting diodes **Mo2.4**
15.45-16.00	Qiang Liu - Study of Low Cost Growth of Large Size Bulk GaN Crystal Growth by a New Vertical HVPE Reactor with Showerhead Nozzle **Mo1.5**	Yuh-Renn Wu - Three Dimensional Simulation on the Transport and Quantum Efficiency of UVC-LEDs with Random Alloy Fluctuations **Mo2.5**
16.00-16.30	**Coffee break**	
16.30-18.30	**Parallel sessions: Growth and Characterization & Optoelectronic Devices**	
	Mo3 - G&CH (chair: **H. Fujioka**)	**Mo4 - OPTO** (chair: **R. Dupuis**)
16.30-17.00	Y. Kumagai - Thermodynamics on HVPE of group-III nitrides **(invited) Mo3.1**	V. Jmerik - Plasma-assisted molecular beam epitaxy of monolayer-thick GaN/AlN heterostructures for high efficient sub-250-nm UV emitters (**invited**) **Mo4.1**
17.00-17.15	T. Schneider - Defect and stress engineering in GaN layers grown by high temperature vapor phase epitaxy **Mo3.2**	Y. Itokazu - UVC LEDs on AlN/sapphire templates prepared by high-temperature annealing and regrowth process **Mo4.2**

17.15-17.30	N. Takekawa - Excess Chlorine and Growth Temperature Effects of N-Polar GaN Growth via Tri-halide Vapor Phase Epitaxy and its Theoretical Study **Mo3.3**	C. De Santi - Investigation of the Thermal Droop in InGaN-based Layers and UVA LEDs **Mo4.3**
17.30-17.45	I. Gamov - Carbon-doped GaN: Identification of tri-carbon defects formed at substantial fraction **Mo3.4**	M. A. Khan - Investigation of crystallinity and current injection issue in 310nm-AlGaN UVB LED grown on AlN template in LP-MOVPE **Mo4.4**
17.45-18.00	F.C. Beyer - Photoluminescence of Carbon-doped HVPE GaN layers **Mo3.5**	M. Jo - UVC emission from (11-22) AlGaN quantum wells grown by metal-organic chemical vapor deposition **Mo4.5**
18.00-18.30	J. Freitas – A new method to achieve efficient iron doping of HVPE GaN substrates **(invited) Mo3.6**	**18.00-18.15** P. Michałowski - Oxygen-induced high diffusion rate of magnesium dopant in GaN/AlGaN based UV LED heterostructures **Mo4.6**

TUESDAY (7TH AUGUST)		
8.30-10.30	**Parallel sessions: Growth and Characterization & Optoelectronic Devices**	
	Tu1 - G&CH (chair: **H. Murakami**)	**Tu2 - OPTO** (chair: **D. Jena**)
8.30-9.00	S. Chichibu - Acidic ammonothermal growth of GaN (**invited**) **Tu1.1**	S. Rajan - Tunnel Junctions for Next Generation III-Nitride Optoelectronics (**invited**) **Tu2.1**
9.00-9.30	M. Zajac - Basic ammonothermal growth of GaN (**invited**) **Tu1.2**	G. Muziol - Long-living laser diodes grown by plasma assisted molecular beam epitaxy (**invited**) **Tu2.2**
9.30-9.45	K. Endo - Fabrication of GaN Crystals with Low Threading Dislocation Density as well as Low Resistivity Grown with Thin-Flux-Growth Method in Na-flux Point Seed Technique **Tu1.3**	N. Chery - Structural Investigation Of InGaN/GaN Heterostructures Quantum Wells For Long Wavelength Emission **Tu2.3**
9.45-10.00	T. Yamada - Reduction of Li impurity in the Freestanding GaN Substrate Fabricated by the Na-Flux Sapphire Dissolution Technique **Tu1.4**	K. Hiraiwa - AlInN/GaN DBRs for Long-wavelength GaN-based VCSELs **Tu2.4**
10.00-10.15	N. Takeda - The effect of undissolved carbon on GaN crystal growth in Na flux method **Tu1.5**	S. Ishimoto - Improvement of emission efficiency in green LEDs by sputtered AlN buffer layer **Tu2.5**
10.15-10.30	Zionglang Liu - Growth of GaN Single Crystal by Na Flux Method Adding Nitrogen-doped Carbon **Tu1.6**	E. Iliopoulos - Kinetic Mechanisms of InGaN(0001) by RF-MBE in the entire composition range: Phenomenological Model and Impact on Epilayer Properties **Tu2.6**
10.30-11.00	**Coffee break**	
11.00-13.00	**Parallel sessions: Growth and Characterization & Electrical Devices**	
	Tu3 - G&CH (chair: **H. Miyake**)	**Tu4 - ELECTRO** (chair: **T. Palacios**)
11.00-11.30	Xinqiang Wang - Growth of InN films with high electron mobility by MBE (**invited**) **Tu3.1**	I. Kizilyalli - Vertical Power Devices based on Bulk GaN Substrates **(invited) Tu4.1**
11.30-12.00	J. Han - Stacking-fault-free (20-2-1) GaN on 4" sapphire substrates: a pathway to commercialize semipolar optoelectronics **(invited**) **Tu3.2**	J. Suda - Electrical characterization of homoepitaxial GaN layers for GaN vertical power devices (**invited**) **Tu4.2**
12.00-12.15	S. Walde - MOVPE grown AlN on nano-patterned sapphire substrates with different offcut angles **Tu3.3**	Y. Tokuda - Characterization of Shallower Level Traps in p-GaN Grown by MOVPE Using Low Frequency Capacitance DLTS **Tu4.3**
12.15-12.30	R. Mantach - Semi polar (10-11) GaN growth on silicon-on-insulator substrates for defect reduction and melt back etching suppression **Tu3.4**	K. Kanegae - Accurate estimation of H1 trap concentration in n-type GaN layers **Tu4.4**
12.30-13.00	M. Sarzynski - InGaN quantum structures on patterned substrates (**invited**) **Tu3.5**	T. Narita - Donor states of carbon in p-type GaN grown by MOVPE (**invited**) **Tu4.5**
13.00-14.00	**Lunch break**	
14.00-16.30	**Parallel sessions: Growth and Characterization & Theory**	
	Tu5 - G&CH (chair: **R. Collazo**)	**Tu6 - THEORY** (chair: **J. Majewski**)

14.00-14.30	C. Hartmann - On the preparation of AlN single crystal boules and substrates, and subsequent epitaxy for AlGaN devices (**invited**) Tu**5.1**	Y. Kangawa - Theoretical study: Impurity incorporation in GaN MOVPE (**invited**) **Tu6.1**
14.30-15.00	H. Miyake - Homoepitaxy of AlN on annealed AlN/sapphire template (**invited**) **Tu5.2**	**S. Krukowski -** Adsorption at nitride semiconductors surfaces - electronic aspects: surface states occupation, the equilibrium pressure, growth and doping (**invited**) Tu6.2
15.00-15.15	I Gamov - Di-carbon defects in AlN bulk crystals grown by physical vapor transport **Tu5.3**	T. Ito - A Simple Theoretical Approach to Growth Mode of III-Nitride Thin Films Tu6.3
15.15-15.30	H. Sun - Tuning the growth of AlN epilayers on Al2O3 via TMAl preflow by MOCVD **Tu5.4**	K. Ohkawa - AlGaN MOVPE Growth Simulation under 10-100 kPa Considering Polymer formation **Tu6.4**
15.30-15.45	H. Yoshida - Controlling the growth mode and strain of AlN grown directly on 6H-SiC(0001) substrate by metal-organic chemical vapor deposition **Tu5.5**	A. Kusaba - Relationship between the CH4 Adsorption Probability and the C Impurity Concentration in the Polar-GaN MOVPE System **Tu6.5**
15.45-16.00	H. Zhang - Hot-wall MOCVD growth of N-polar AlN nucleation layer on C-face vicinal and on-axis SiC substrates **Tu5.6**	P. Kempisty - Contribution of first principles phonon calculations to thermodynamics analysis of GaN surfaces **Tu6.6**
16.00-16.15	K. Uesugi - Crystal quality improvement of sputter-deposited AlN films on SiC substrates by high temperature annealing **Tu5.7**	J. Endres - Kinetic Monte Carlo simulation of MOVPE growth/sublimation of GaN on the vicinal GaN(0001) substrate **Tu6.7**
16.15-16.30	M. Fijalkowski - Growth of thick AlGaN layers by HVPE method on GaN seeds **Tu5.8**	P.Strak - Catalytic potential of AlN(0001) surface for N2 + H2 ammonia synthesis reaction **Tu6.8**
16.40-17.40	**Tutorial session** **TS** (chair: **L. Kirste**)	
16.40-17.10	L. Grieger - Williamson-Hall Analysis on Epilayers – A critical review of common practice **(invited) TS1**	
17.10-17.40	M. Leszczyński - X-ray Diffraction in Nitride Technology- most common mistakes and new opportunities **(invited) TS2**	
18.00-21.00	**Poster Session** (chair: **M. Bockowski**)	

WEDNESDAY (8TH AUGUST)		
8.30-10.10	**Plenary Session 3** **PS3 (**chair: **I. Grzegory**)	
8.30-9.20	Y. Mori - Recent Progress of GaN Growth by Na-flux Method **(plenary) PS3.1**	
9.20 – 10.10	C.G. Van de Walle - Acceptors in nitrides: doping, compensation, and impact on device performance **(plenary) PS3.2**	
10.10-10.30	**Coffee break**	
10.30-13.00	**Parallel sessions: Characterization & Theory**	
	We1 - CH (chair: **M. Leszczynski**)	**We2-THEORY** (chair: **S. Krukowski**)
10.30-11.00	L. Kirste - Defect Structure Analysis of GaN Substrates by Synchrotron X-Ray Diffraction Techniques (**invited**) **We1.1**	A. Toropov - Optical properties of 1ML GaN in AlN: what happens beyond the envelope function approach (**invited**) **We2.1**
11.00-11.30	R. Oliver - Multi-microscopy of defects in nitride semiconductors (**invited**) **We1.2**	K. Shiraishi - First Principles and Thermodynamic Studies on GaN MOVPE Processes (**invited**) **We2.2**
11.30-12.00	P. Ruterana - Spontaneous formation of quantum wells, ordering and composition fluctuations in (11-22) semipolar AlGaN/GaN heterostructures grown by plasma enhanced MBE (**invited**) **We1.3**	D. Irving - Compensation in Si-doped AlN: Mechanisms and opportunities (**invited**) **We2.3**
12.00-12.15	Y. Yao - Observation of Dislocations in AlN Single Crystal by Using Synchrotron X-Ray Topography, Etch Pit Method and Transmission Electron Microscope **We1.4**	Y. Inatomi - A theoretical model for carbon incorporation during step-flow growth of GaN by MOVPE **We2.4**
12.15-12.30	Lok Yi Lee - Investigation of Stacking Faults in Zincblende GaN Grown on 3C-SiC on Si templates with TEM and XRD **We1.5**	M. Wierzbowska- Perovskite Solar Cells with n-type GaN Electrodes **We2.5**
12.30-12.45	K. Shida - Nanobeam X-ray Diffraction Analysis of Local Lattice Distortions in the Growth Direction of a Modified Na-Flux GaN Bulk Crystal **We1.6**	**12.30-13.00** A. Jamroz - Morphology and Electronic Structure of Carbon Doped Hexagonal Boron Nitride (**invited**) **We2.6**
12.45-13.00	J. Stranska-Matejova - Strain relaxation in InGaN/GaN epilayers by formation of V-pit defects: XRD experiments and numerical simulations **We1.7**	
13.00-14.00	**Lunch break**	
14.00-18.00	**Excursion**	
19.30-22.00	**Gala Dinner**	

THURSDAY (9TH AUGUST)		
9.00-11.00	**Parallel sessions: Electrical Devices & Characterization**	
	Th1- ELECTRO (chair: **T. Anderson**)	**Th2 - CH** (chair: **M. Kamińska**)
9.00-9.30	T. Palacios - GaN Nanostructures (or how to Take Transistor Linearity to new Levels) (**invited**) **Th1.1**	T. Tanikawa - Two-photon-excitation photoluminescence and its recent progress (**invited**) **Th2.1**
9.30-10.00	D. Jena - Growth, Physics, and Applications of Tunneling Nitride Structures (**invited**) **Th1.2**	A. Tanaka - Observation of Dislocation Propagation in GaN on GaN Structure with a Multiphoton Excitation Photoluminescence Microscope (**invited**) **Th2.2**
10.00-10.15	Z. Feng - High Reliability and Frequency Performances of InAlN/GaN HFETs **Th1.3**	**10.00- 10.30** M. Sumiya - Evaluation of Structural Disorder and In-Gap States of III-V nitrides by Photothermal Deflection Spectroscopy (**invited**) **Th2.3**
10.15-10.30	R. Tanaka - Demonstration of GaN vertical double implanted MOSFET **Th1.4**	
10.30-10.45	F. Bouazzaoui - Optimized Ohmic Contacts For InAlGaN/GaN HEMTs **Th1.5**	A. Kaminska - Origin of the Yellow Luminescence in Be-doped GaN revealed by hydrostatic pressure studies **Th2.4**
10.45-11.00	I. Sanyal - Improving the Performance of AlInN/GaN and AlInGaN/GaN HEMTs by Using a Triethylgallium-Grown Channel Layer and Barrier **Th1.6**	K. K. Madapu - Imaging of Surface Plasmon Polaritons of 2D Plasmons of InN Nanostructures having Surface Electron Accumulation **Th2.5**
11.00-11.15	**Coffee break**	
11.15-13.00	**Parallel sessions: Electrical Devices & Nanowires**	
	Th3-ELECTRO (chair:**C.Skierbiszewski**)	**Th4-NANO** (chair: **Xinqiang Wang**)
11.15-11.45	T. Anderson - Navy Application of Wide Bandgap (WBG) semiconductors enabling future Power and Energy Systems **(invited) Th3.1**	**11.15-11.30** M. Takebayashi - Fabrication and characterization of GaN nanowires optoelectronic devices **Th4.1**
		11.30-11.45 M. Terazawa - Optical simulation of GaInN-based multi-quantum-shell (MQS)-Light-Emitting-Diodes (LEDs) **Th4.2**
11.45-12.15	J. Hite - Vertical Power Devices Enabled by Bulk GaN Substrates (**invited**) **Th3.2**	**11.45-12.00** G. Avit - Self-Induced InGaN Nanowires with a Controlled Indium Composition and Selective Area Growth of InN by HVPE **Th4.3**
		12.00 -12.15 N. Goto - Study on emission wavelength control of GaInN multi-quantum-shell/GaN nanowire **Th4.4**
12.15-12.30	M. Takahashi - Characterizations of high-temperature Mg ion implantation in GaN **Th3.3**	A. Suzuki - Device fabrication of GaInN-based multi-quantum-shell LEDs **Th4.5**
12.30-12.45	H. Sakurai - Non-cap thermal activation process of Mg-ion implanted Ga-polar	A Kapoor - Green/Yellow/Red Emission From m-plane Core-shell InGaN/GaN Nanowires **Th4.6**

	GaN using ultra high pressure N2 annealing **Th3.4**	
12.45-13.00	M. Deki - Improvement of Electrical Stability of ALD-Al2O3/GaN Interface by UV/O3 Oxidation and Postdeposition Annealing **Th3.5**	H. Zhou - Insights into the Quantum Efficiency and Recombination Dynamics of InGaN/GaN Core-Shell Microrod LED Structures **Th4.7**
13.00-14.00	**Lunch break**	
14.00-16.00	**Parallel sessions: Growth and Characterization & Optoelectronic Devices and Growth**	
	Th5- G&CH (chair: **J. Hite**)	**Th6 - OPTO&G** (chair: **J. Freitas**)
14.00-14.15	Y. Yamagata - In-situ observation of AlN growth on levitated Ni-Al droplet **Th5.1**	Xiaohang Li- Significantly enhanced performance for AlGaN UV LED by employing a thin BAlN electron blocking layer (**invited**) **Th6.1**
14.15-14.30	M. Noorprajuda - Effect of Reaction Temperature on AlN Formation at Interface of Al Layer Deposited on GaN Substrate **Th5.2**	
14.30-14.45	Y. Mogami - Evolution of morphology and crystalline quality of sputtered AlN films with high-temperature annealing **Th5.3**	P. Dróżdż - Green - blue InGaN/GaN LED array obtained by lateral band-gap engineering **Th6.2**
14.45-15.00	T. Fudetani - Characteristics of highly conductive p-type GaN films prepared by pulsed sputtering **Th5.4**	M. Sawicka - InAlN growth peculiarities on vicinal GaN substrates **Th6.3**
15.00-15.15	M. Sakamoto - Improvement of electron mobility of polycrystalline InN on glass substrates by AlN buffer layers **Th5.5**	M. Deppe - Germanium doping of Cubic AlxGa1-xN Grown by Molecular Beam Epitaxy **Th6.4**
15.15-15.30	Y. Sakurai - Structural and Electrical Properties of AlN and AlGaN Prepared by Pulsed Sputtering **Th5.6**	V. Zubialevich - Material Redistribution during Thermal Annealing of GaN Nanocolumns and Conditions for Their Maskless Overgrowth by MOVPE **Th6.5**
15.30-15.45	M. Mazraehno - Surface Morphology Control and Si-Doping of MOVPE-Grown High-Al-Content AlGaN Layers **Th5.7**	J. Kierdaszuk - Surface-enhanced Raman scattering in graphene induced by AlxGa1-xN/GaN axial heterostructure nanowire substrate **Th6.6**
15.45-16.00	X. Shen- Effects of N2 and H2 carrier gases on the growth of AlGaN epilayers on Si(110) substrates by MOCVD **Th5.8**	K. Sasai - Two-step epitaxial growth of GaN nanowires by MOVPE **Th6.7**
16.00-16.30	**Coffee break**	
16.30-18.30	**Parallel sessions: Electrical Devices & Boron Nitride and Related Materials**	
	Th7 - ELECTRO (chair: **M. Deki**)	**Th8-BN** (chair: **D. Hommel**)
16.30-17.00	G. Cywinski -EdgeFET Devices Fabricated on 2DEG GaN/AlGaN Heterostructures for Basic and Applied Sciences **(invited) Th7.1**	**16.30 - 16.45** J. Baranowski - MOCVD of Boron Nitride Films on Sapphire **Th8.1**
		16.45-17.00 K. Pakuła - Investigation of MOVPE Boron Nitride Growth **Th8.2**

17.00-17.15	P. Sai - AlGaN/GaN EdgeFET Based on Two Lateral Schottky Barrier Gates as Terahertz Detector **Th7.2**	F. Liu - Growth of BN thin films by MBE: effect of post thermal annealing **Th8.3**
17.15-17.30	A. Yamamoto - A Study on 2DEG Properties of AlGaN/GaN Structures Formed on Stepped GaN Surfaces for Vertical Power Devices **Th7.3**	**17.15-17.45** A. Wysmołek - Excitonic spectra of ultra-thin epitaxial boron nitride layers grown by MOCVD (**invited**) **Th8.4**
17.30-17.45	Yung-Ting Ho - Modified Small-Signal Model for High Frequency GaN-on-Si HEMT with the Leaky Buffer **Th7.4**	
17.45-18.00	Y. Ando - Schottky Barrier Diodes Fabricated on Miscut m-plane Substrates **Th7.5**	H. Sun - Novel BAlN/AlxGa1-xN heterostructures for optical and power devices **Th8.5**
18.00-18.15	E. Lutsenko - AlGaN/GaN HEMT Heterostructures Grown by Ammonia and Combined Plasma-Assisted/Ammonia MBE on Sapphire Substrates **Th7.6**	U. Ooe - Nitrogen Plasma Effects on MBE Growth of GaN on Graphitic Substrate **Th8.6**
18.15-18.30		J. Schmitt - New AlScN growth and annealing for used as lattice matched substrate for deep UV LEDs **Th8.7**

FRIDAY (10TH AUGUST)		
8.30-10.15	**Parallel sessions: Characterization & Electrical Devices**	
	Fr1 - CH (chair: **R. Oliver**)	**Fr2 - ELECTRO** (chair: **G. Cywinski**)
8.30-9.00	M. Albrecht - InGaN still to be discovered **(invited) Fr1.1**	A. Yamada - Ultralow-sheet-resistance high-electron-mobility transistor structures with strain-controlled high-Al-composition AlGaN barrier (**invited**) **Fr2.1**
9.00-9.30	J. Smalc-Koziorowska - Differences in the mechanism of strain relaxation of InGaN buffer layers deposited on GaN/sapphire templates and GaN bulk substrates (**invited**) **Fr1.2**	**9.00-9.15** T. Hamachi - Leakage current analysis for individual dislocations in the modified Na-flux GaN bulk single crystal **Fr2.2**
		9.15-9.30 S. Usami - Dependency of the reverse leakage current on the MOVPE growth pressure of vertical p–n diodes on a GaN free-standing substrate **Fr2.3**
9.30-9.45	R. Mohamad - Investigation of the spontaneous crystallographic degradation in nearly lattice-matched InAlN layers to GaN **Fr1.3**	K. Matsumoto - Reduction of Carrier Concentration Increase near the Surface of Silicon Substrate after GaN Growth **Fr2.4**
9.45 – 10.00	J. Moneta - The Upper Limit for InGaN Plastic Relaxation – Could We Obtain Fully Relaxed InGaN Layer? **Fr1.4**	Yu-En Jeng - RF-Loss Suppression of AlGaN/GaN-on-Si HEMT With Superlattice Buffer **Fr2.5**
10.00-10.15	A. Lachowski - Structural Studies of the Processes Occurring During Thermal Annealing of InGaN Quantum Wells **Fr1.5**	JunShuai Xue- Growth and Characterization of InAlN/AlGaN Heterostructures **Fr2.6**
10.15-10.45	**Coffee break**	
10.45-12.15	**Parallel sessions: Growth and Characterization & Optoelectronic Devices**	
	Fr3 - G&CH (chair: **J. Baranowski**)	**Fr4 -OPTO** (chair: **S. Chichibu**)
10.45-11.15	L. Janicki - Determination of the Fermi Level in Doped GaN by Contactless Electroreflectance (**invited**) **Fr3.1**	Mi-Hee Ji - Growth and Device Characterization of III-N Deep-Ultraviolet Avalanche Photodiodes and Arrays (**invited**) **Fr4.1**
11.15-11.30	H. Turski - Alloying as an effective way to increase Mg incorporation into GaN **Fr3.2**	S. Zlotnik - Alternative Growth Approaches of p-Type Doped AlGaN Epitaxial Structures **Fr4.2**
11.30-11.45	B. Rackauskas - Self-Compensation of Carbon in AlGaN **Fr3.3**	A. Hospodkova - Design of InGaN/GaN MQW structure for scintillator applications **Fr4.3**
11.45-12.15	R. Collazo - Controlling Si Doping Limits in Al Rich AlGaN: Knee Behavior and Low Doping Limits (**invited**) **Fr3.4**	N. Grandjean - Burying surface defects in InGaN underlayer to increase blue LED efficiency **(invited**) **Fr4.4**
12.30-13.00	**Closing Ceremony** (chair: I. Grzegory and Y. Nanishi)	
13.00-14.00	**Lunch**	

	POSTER SESSION (TUESDAY 7TH AUGUST, 18.00-21.00)
Po01	Raman Spectroscopic Study of GaN Grown on (111)Si Using an AlInN Intermediate Layer by MOVPE, T. Sugiura et al., National Institute of Technology, Toyota College, Japan
Po02	InGaN Band Gap Compositional Dependence Determined by Means of Photoacoustic Spectroscopy, R.Oliva Vidal et al., Politechnika Wrocławska, Poland
Po03	TEM Investigations on High-Temperature Annealed epi-AlN on Sapphire, L. Cancellara et al., Leibniz-Institute for Crystal Growth, Germany
Po04	Diffusion and out-diffusion of Mn in gallium nitride, R. Jakieła et al., Istitute of Physics Polish Academy of Sciences, Poland
Po05	Impact of Si doping in different GaN layers on luminescence properties of InGaN/GaN multiple quantum well structure, F. Hájek et al., Institute of Physics, Czech Academy of Science, Czech Republic
Po06	Optical modulation spectroscopy of AlxGa1-xN epilayers and AlxGa1-xN/GaN quantum wells in the UV spectral range, E. Zdanowicz et al., Wrocław Research Center EIT+, Poland
Po07	Excess Carrier Lifetime in Ammonothermal GaN Doped with Si, Mg, and Mn, Ł. Janicki et al., Wrocław University of Science and Technology, Poland
Po08	Influence of Depletion Layer on Spatial Distribution of Cathodoluminescence Intensity in GaN Nanowires, B. Adamowicz et al., Institute of Physics - CND, Silesian University of Technology, Poland
Po09	Influence of Macrosteps on Deep-ultraviolet Emission from AlGaN/AlGaN Multiple Quantum wells, K. Kataoka et al., Toyota Central R&D Labs., Inc., Japan
Po10	Growth of InGaN Films by Reactive Sputtering, Q. Guo et al., Saga University, Japan
Po11	High temperature vapor phase epitaxy for the growth of GaN layers on sapphire substrates, M. Förste et al., Institute of Nonferrous Metallurgy and Purest Materials, TU Bergakademie Freiberg, Germany
Po12	Study of Indium Incorporation in OMVPE Grown 200-nm Thick InxAl1-xN Layers, S. Hasenöhrl et al., Institute of Electrical Engineering, Slovak Academy of Sciences, Slovakia
Po13	Structure of AlN films formed by nitriding the aluminum metal layers on the (0001) sapphire substrates, A. Muslimov et al., Federal Research Center “Crystallography and Photonics”, RAS, Russia
Po14	AlN layers grown by Ga-Al liquid phase epitaxy on nitrided r-plane sapphire substrate, N. Kanno et al., Tohoku University, Japan
Po15	HVPE Growth Method for Thick AlN Epilayer, H. Soo Ahn et al., Korea Maritime and Ocean University, Korea (South)
Po16	Mg-doped AlN Epilayer Grown by Mixed Source HVPE Method, H. Soo Ahn et al., Korea Maritime and Ocean University, Korea (South)
Po17	The Growth of High Al Composition AlxGa1-xN Epilayers, Hyung Soo Ahn et al., Korea Maritime and Ocean University, Korea (South)
Po18	Characteristics of Epilayers in Light Emitting Diode Grown by HVPE Method, H. Soo Ahn et al., Korea Maritime and Ocean University, Korea (South)
Po19	Characteristics of aluminum nitride films on hexagonal boron nitride buffer layers using various growth methods through metal organic chemical vapor deposition, M. Han et al., Chonbuk National University, Korea (South)
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